

WE CLAIM:

1. A semiconductor device comprising:

an integrated circuit chip having an outline, active
and passive surfaces, and active components
including a plurality of contact pads, spaced
apart by less than 100 μm center to center, on
said active surface;

a plurality of electrical coupling members attached
to said contact pads, said coupling members
selected from a group consisting of gold bumps,
copper bumps, copper/nickel/palladium bumps, and
z-axis conductive epoxy;

an electrically insulating thin-film interposer
having first and second surfaces, a plurality of
electrically conductive lines integral with said
first surface, a plurality of electrically
conductive paths extending through said
interposer, contacting said conductive lines and
forming exit ports on said second surface;

said chip coupling members attached to said
conductive lines, covering an area portion of
said first interposer surface; and

encapsulation material protecting said passive chip
surface and at least a portion of said first
interposer surface not covered by said attached
chip.

2. The device according to Claim 1 further having solder
balls attached to said exit ports on said second
interposer surface.

3. The device according to Claim 1 further having an
adhesive non-conductive polymer underfilling any spaces

between said chip coupling members attached to said conductive lines under said chip.

4. The device according to Claim 1 wherein said interposer is a polyimide film.

5. The device according to Claim 1 wherein said interposer has an outline larger than said outline of said chip.

6. The device according to Claim 1 wherein said electrically conductive lines are made of a material selected from a group consisting of copper, copper alloy, or copper plated with tin, tin alloy, silver, or gold.

7. The device according to Claim 1 wherein said coupling member attachment is provided by metal interdiffusion of thermo-compression bonding.

8. The device according to Claim 1 wherein said encapsulation material is a molding compound.

9. The device according to Claim 9 wherein said molding compound has the same outline as said interposer.

10. A semiconductor device comprising:

an integrated circuit chip having an outline, active and passive surfaces, and active components including a plurality of contact pads on said active surface;

a plurality of electrical coupling members attached to said contact pads, said coupling members selected from a group consisting of gold bumps, copper bumps, copper/nickel/palladium bumps, and z-axis conductive epoxy;

an electrically insulating thin-film interposer having first and second surfaces, a plurality of electrically conductive lines integral with said first surface, a plurality of electrically

conductive paths extending through said
interposer, contacting said conductive lines and
forming exit ports on said second surface;
said chip coupling members attached to said
5 conductive lines, covering an area portion of
said first interposer surface; and
encapsulation material protecting said passive chip
surface and at least a portion of said first
interposer surface not covered by said attached
10 chip.

11. A method of assembling an integrated circuit device,
comprising the steps of:

depositing an electrical coupling member of gold,
copper, or copper/nickel/palladium on each
15 contact pad of a circuit chip having pads spaced
apart by less than 100 μm , center to center;
forming an electrically insulating thin-film
interposer by depositing and patterning a
plurality of electrically conductive lines on a
20 first surface thereof;

creating a plurality of electrically conductive
paths extending through said interposer;
contacting said conductive lines on said first
surface and forming exit ports on a second
25 surface of said interposer;

assembling the active surface of said chip onto said
first interposer surface such that each of said
coupling members is attached to one of said
lines, respectively, thereby covering an area
30 portion of said first interposer surface;
encapsulating, with a polymer compound, the passive
surface of said chip and at least a portion of

said interposer surface not covered by said
attached chip, thereby creating a composite
structure having rigidity; and
separating the resulting composite structure into
discrete units.

12. The method according to Claim 11 further comprising the
step of:

underfilling an adhesive non-conductive polymer into
any spaces between said chip coupling members
under said chip, which have been formed by said
step of assembling said chip onto said
interposer, thereby strengthening said assembly.

13. The method according to Claim 11 further comprising the
step of:

attaching solder balls to said exit ports on said
second interposer surface, after completing said
step of encapsulating and before said step of
separating.

14. The method according to Claim 11 wherein said step of
depositing comprises plating, electro-plating,
sputtering, or evaporating.

15. The method according to Claim 11 wherein said step of
separating comprises the steps singulating, trimming
and forming said composite structure.

16. The method according to Claim 11 wherein said step of
assembling comprises the method of thermo-compression
gang bonding said chip coupling members onto said
interposer lines.